

Dispersion Relations in Heavily-Doped Nanostructures

Ghatak, Kamakhya Prasad.,

author

Springer International Publishing:

Imprint: Springer,

2016

Libros electrónicos Recursos electrónicos

Monografía

This book presents the dispersion relation in heavily doped nano-structures. The materials considered are III-V, II-VI, IV-VI, GaP, Ge, Platinum Antimonide, stressed, GaSb, Te, II-V, HgTe/CdTe superlattices and Bismuth Telluride semiconductors. The dispersion relation is discussed under magnetic quantization and on the basis of carrier energy spectra. The influences of magnetic field, magneto inversion, and magneto nipi structures on nano-structures is analyzed. The band structure of optoelectronic materials changes with photo-excitation in a fundamental way according to newly formulated electron dispersion laws. They control the quantum effect in optoelectronic devices in the presence of light. The measurement of band gaps in optoelectronic materials in the presence of external photo-excitation is displayed. The influences of magnetic quantization, crossed electric and quantizing fields, intense electric fields on the on the dispersion relation in heavily doped semiconductors and super-lattices are also discussed. This book contains 200 open research problems which form the integral part of the text and are useful for graduate students and researchers. The book is written for post graduate students, researchers and engineers

Título: Dispersion Relations in Heavily-Doped Nanostructures by Kamakhya Prasad Ghatak

Edición: 1st ed. 2016

Editorial: Cham Springer International Publishing Imprint: Springer 2016

Descripción física: 1 recurso en línea LV, 625 p. 31 illus

Mención de serie: Springer Tracts in Modern Physics 0081-3869 265 Springer eBooks

Contenido: From the Contents: The DR in Quantum Wells (QWs) of Heavily Doped(HD) Non-Parabolic

Semiconductors -- The DR in Nano-Wires (NWs) of Heavily Doped (HD) Non-Parabolic Semiconductors -- The

DR in Quantum Box (QB) of Heavily Doped (HD) Non-Parabolic Semiconductors -- The DR in doping superlattices of HD Non-Parabolic Semiconductors -- The DR in Accumulation and Inversion Layers of Non-Parabolic Semiconductors

Detalles del sistema: Modo de acceso: World Wide Web

ISBN: 9783319210001

Materia: Physics Solid state physics Nanoscale science Nanoscience Nanostructures Semiconductors Microwaves Optical engineering Nanotechnology Physics Semiconductors Nanotechnology Microwaves, RF and Optical Engineering Nanoscale Science and Technology Solid State Physics

Entidades: SpringerLink (Online service)

Punto acceso adicional serie-Título: Springer Tracts in Modern Physics 0081-3869 265

Baratz Innovación Documental

- Gran Vía, 59 28013 Madrid
- (+34) 91 456 03 60
- informa@baratz.es